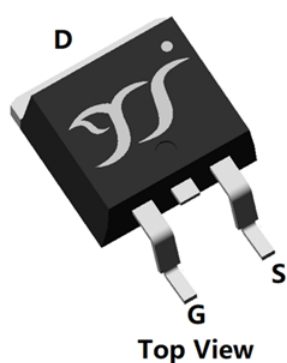
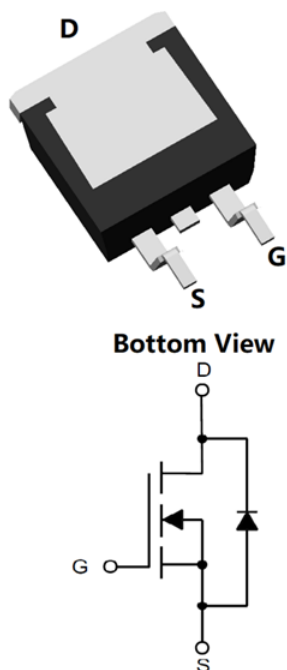


N-Channel Enhancement Mode Field Effect Transistor



TO-263



Product Summary

- V_{DS} 60V
- I_D 200A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <2.9 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <3.9 mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Consumer electronic power supply
- Isolated DC-DC Converters
- Motor control
- Invertors

■ Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current ^A	$T_C=25^{\circ}C$	I_D	200	A
	$T_C=100^{\circ}C$		125	
Pulsed Drain Current ^B		I_{DM}	600	A
Avalanche energy ^C		EAS	506	mJ
Total Power Dissipation ^D		P_D	260	W
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	0.48	$^{\circ}C/W$
Thermal Resistance Junction-to-Ambient ^E		$R_{\theta JA}$	28	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^{\circ}C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB200G06C	F2	YJB200G06C	800	/	8000	13" reel



YJB200G06C

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.2	1.6	2.2	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D =20A		2.35	2.9	mΩ
		V _{GS} = 4.5V, I _D =15A		2.9	3.9	
Diode Forward Voltage	V _{SD}	I _S =20A,V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				200	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V,f=100KHZ		5950		pF
Output Capacitance	C _{oss}			1250		
Reverse Transfer Capacitance	C _{rss}			85		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V,V _{DS} =50V,I _D =50A		93		nC
Gate-Source Charge	Q _{gs}			17		
Gate-Drain Charge	Q _{gd}			14		
Reverse Recovery Chrage	Q _{rr}	I _F =25A, di/dt=100A/us		73		
Reverse Recovery Time	t _{rr}			68		
Turn-on Delay Time	t _{d(on)}	V _{GS} =10V,V _{DD} =30V,I _D =25A R _{GEN} =2Ω		22.5		ns
Turn-on Rise Time	t _r			6.7		
Turn-off Delay Time	t _{d(off)}			80.3		
Turn-off fall Time	t _f			26.9		

Note:

- The maximum current rating is package limited.
- Repetitive rating; pulse width limited by max. junction temperature.
- T_J=25℃, V_{DD}=80V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=45A.
- P_D is based on max. junction temperature, using junction-case thermal resistance.
- The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 ℃.



■ Typical Performance Characteristics

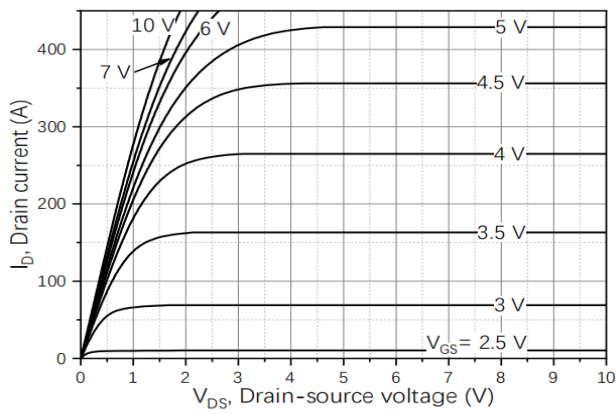


Figure1. Output Characteristics

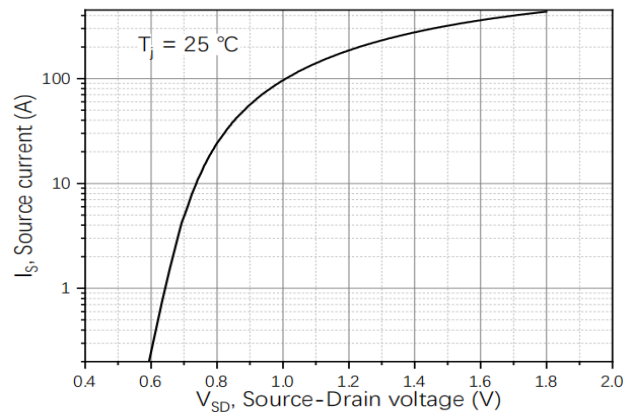


Figure2. Transfer Characteristics

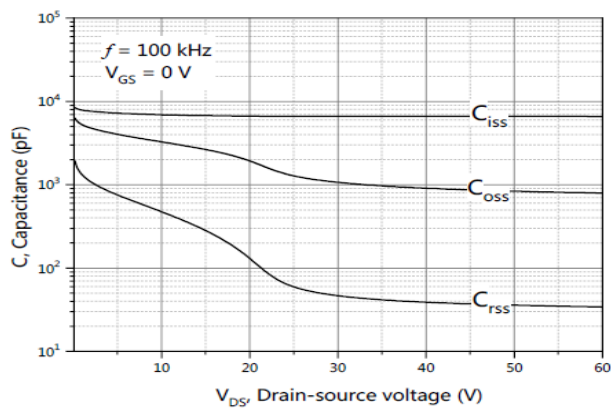


Figure3. Capacitance Characteristics

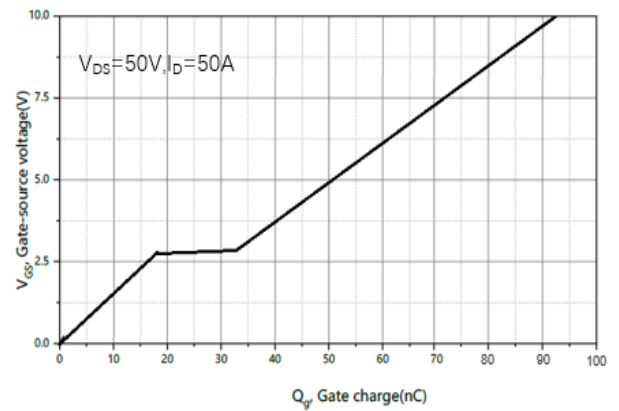


Figure4. Gate Charge

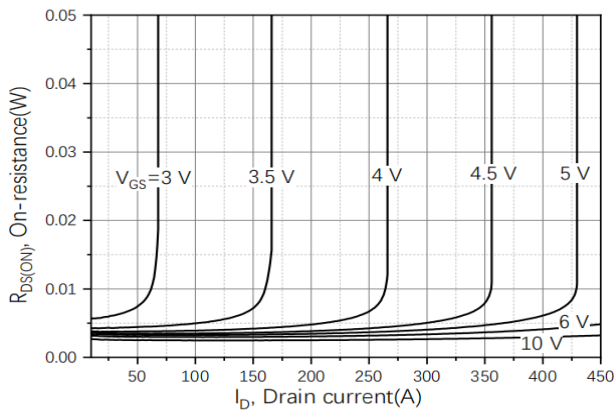


Figure5. Drain-Source on Resistance

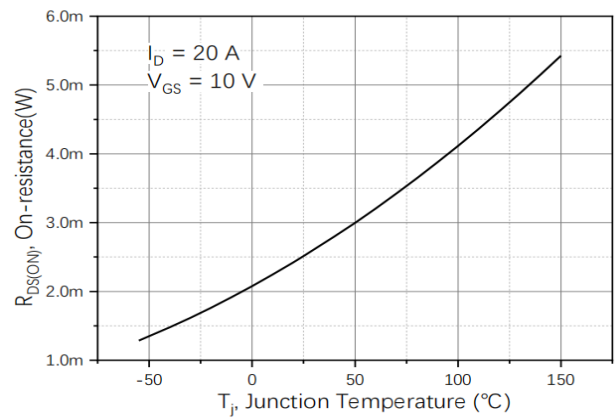


Figure6. Drain-Source on Resistance

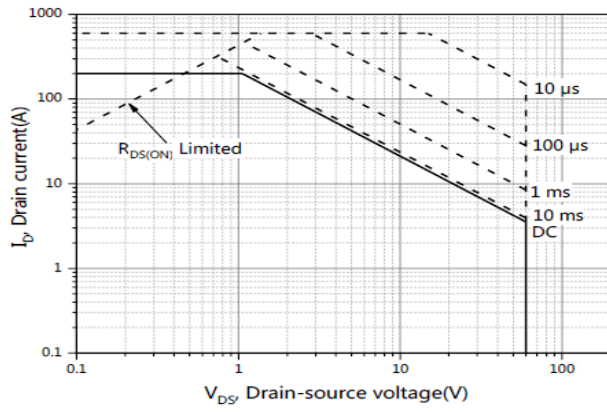


Figure7. Safe Operation Area

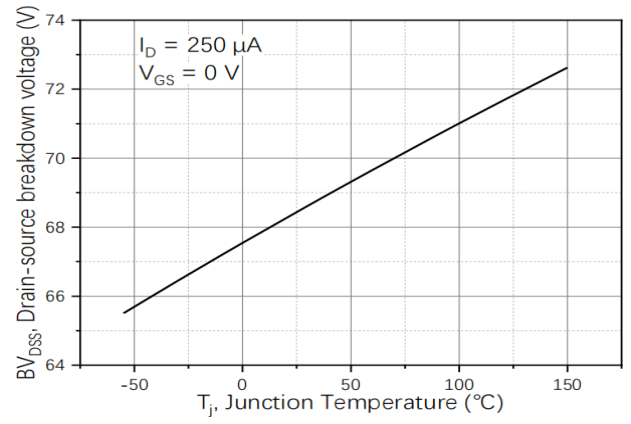


Figure8. Drain-source breakdown voltage

■ Test circuits and waveforms

Figure A: Gate Charge Test Circuit & Waveforms

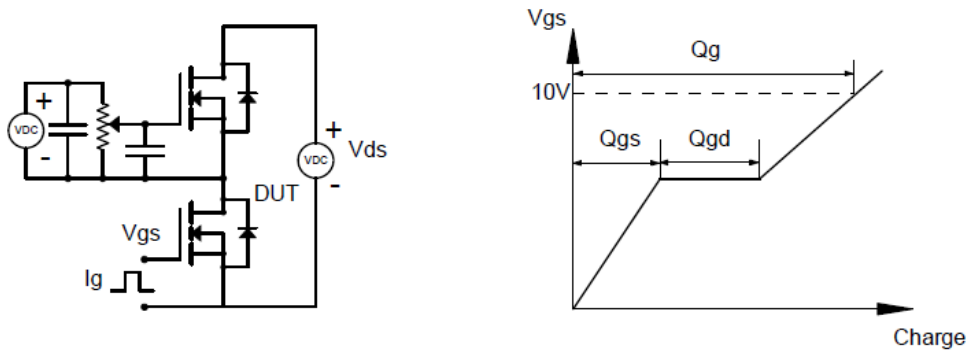


Figure B: Resistive Switching Test Circuit & Waveforms

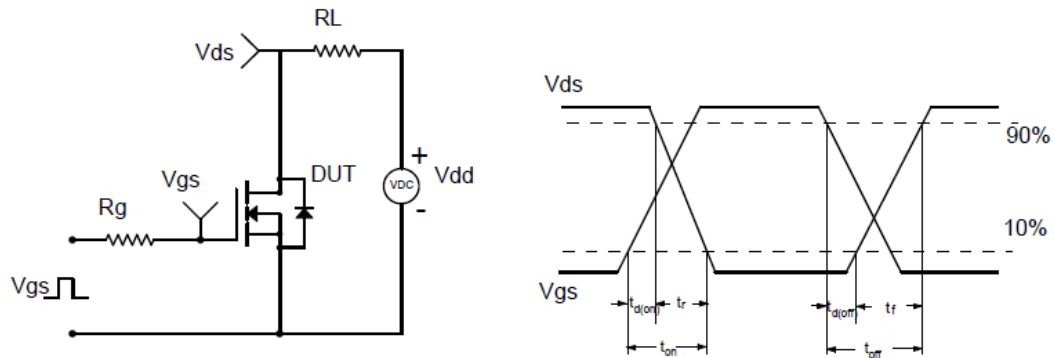


Figure C: Unclamped Inductive Switching (UIS) Test

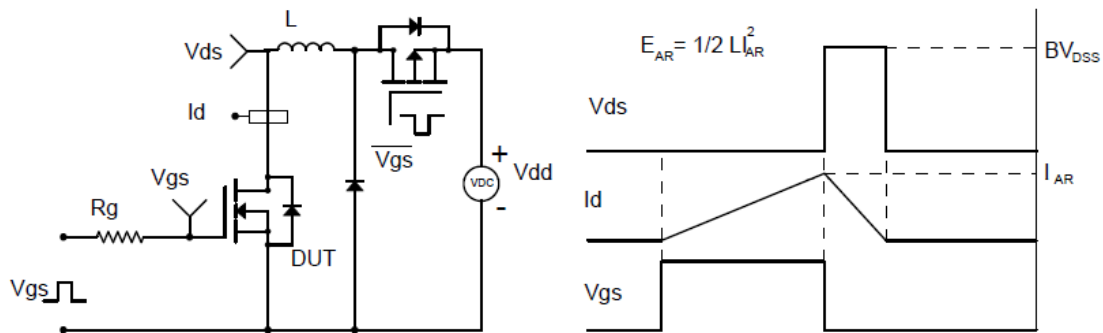
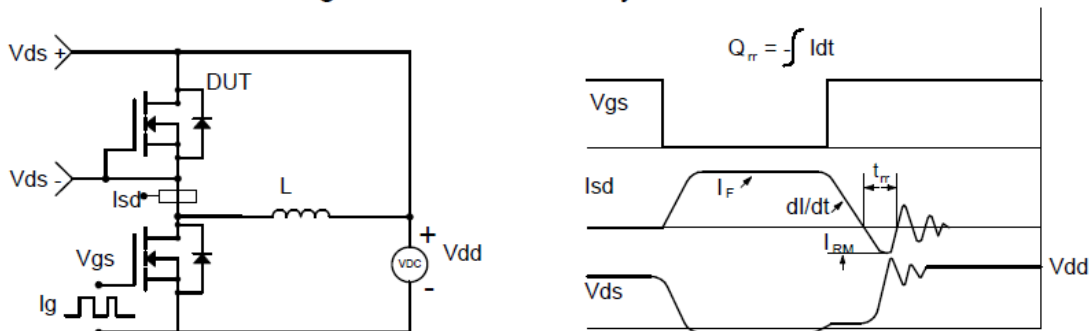


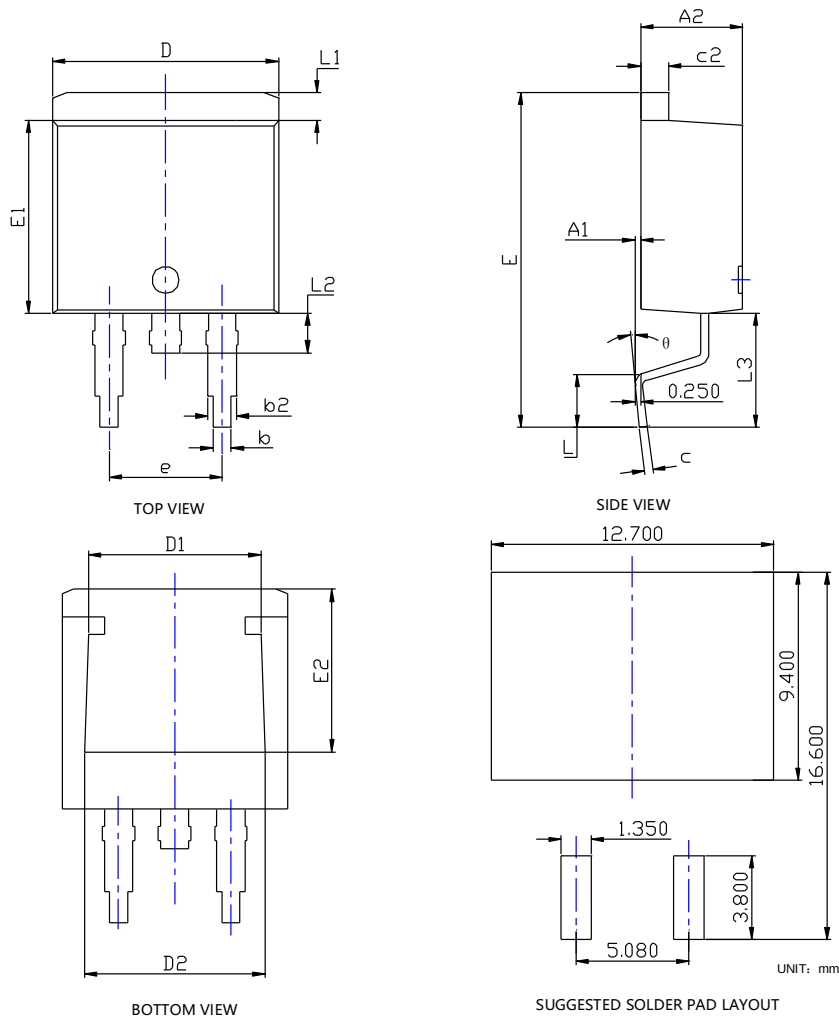
Figure D: Diode Recovery Test Circuit & Waveforms





YJB200G06C

■ TO-263-HY Package information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.340
D	0.394	0.400	0.406	10.000	10.150	10.300
D1	0.295	0.307	0.319	7.500	7.800	8.100
D2	0.303	0.315	0.327	7.700	8.000	8.300
E	0.571	0.591	0.610	14.500	15.000	15.500
E1	0.337	0.341	0.348	8.550	8.700	8.850
E2	0.276	0.287	0.299	7.000	7.300	7.600
e	0.200BSC			5.080BSC		
L	0.070	---	0.110	1.790	---	2.790
L1	0.044	---	0.056	1.120	---	1.420
L2	0.030	---	0.070	0.770	---	1.770
L3	0.197REF			5.000REF		
θ	0°	---	8°	0°	---	8°

NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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